

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)				Attorney Docket No.: 8028-1160		Application No.: NEW NATIONAL PHASE	
				Applicant: Ryuji KOBAYASHI			
				Filing Date: May 26, 2006		Group Art Unit:	

U.S. PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing date (if appropriate)
/X.N./	6,337,870	1/8/2002	Furushima			
/X.N./	5,671,242	9/23/1997	Takiguchi et al.			

FOREIGN PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
/X.N./	11-121858	4/30/1999	JAPAN				
/X.N./	8-78786	3/22/1996	JAPAN				
/X.N./	2003-133647	5/9/2003	JAPAN				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
/X.N./	SAKATA, Y. et al., 'All-selective MOVPE-grown 1.3- μ m strained multi-quantum-well buried-heterostructure laser diodes', In: IEEE Journal of Quantum Electronics, Vol. 35, 3 rd issue, March 1999, pages 368 to 376
/X.N./	Wang, M.C. et al., 'Ultrahigh temperature and ultrahigh speed operation of 1.3 μ m strain-compensated AlGaInAs/InP uncooled laser diodes', In: Electronics Letters, Vol. 31, 18 th issue, 31 August, 1995 (31.08.95), pages 1584 to 1585
/X.N./	TSUCHIYA, T. et al., 'Large number of periods in highly strained InGaAlAs/InGaAlAs MQW structures grown by metalorganic vapor-phase epitaxy', International Conference on Indium Phosphide and Related Materials, Technical Summary, p. 47, MoB1-2, May 16, 1999
/X.N./	Electronics Letters Vol. 27, No. 14, pp. 1268 to 1270, 1991
/X.N./	MILLER, B.I. et al., 'Strain-compensated strained-layer superlattices for 1.5 μ m wavelength lasers', Applied Physics Letters Vol. 58, pp. 1952 to 1954, 1991
/X.N./	Electronics Materials, pp. 32 to 36, November, 1991
/X.N./	SAKATA, Y. et al., 'Selective MOVPE Growth of InGaAsP and InGaAs Using TBA and TBP', Journal of Electronic Materials Vol. 25, No. 3, pp. 401 to 406, 1996
/X.N./	MINCH, J. et al., 'Theory and Experiment of In1-xGaxAsyP1-y and In1-x-yGaxAlyAs Long-Wavelength Strained Quantum-Well Lasers, IEEE Journal of Quantum Electronics Vol. 35, pp.771 to 782, 1992
/X.N./	MATTHEWS, J.W. et al., 'Defects in epitaxial multilayers', Journal Crystal Growth Vol. 27, pp. 118 to 125, 1974
EXAMINER: /Xinning Niu/ DATE CONSIDERED 11/29/2007	

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

* English language abstract provided for the Examiner's convenience